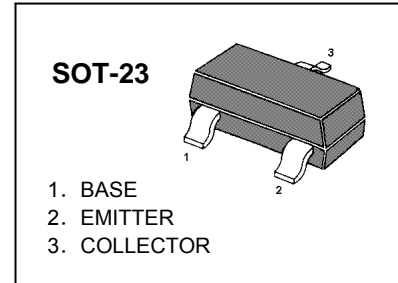


BC817 TRANSISTOR(NPN)

FEATURE

- ◆ For general AF applications
- ◆ High collector current
- ◆ High current gain
- ◆ Low collector-emitter saturation voltage
- ◆ Complementary types: BC807 (PNP)



MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	50	V
V_{CEO}	Collector-Emitter Voltage	45	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.5	A
P_C	Collector Power Dissipation	0.3	W
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V_{CBO}	$I_C = 10\mu\text{A}, I_E = 0$	50			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = 10\text{mA}, I_B = 0$	45			V
Emitter-base breakdown voltage	V_{EBO}	$I_E = 1\mu\text{A}, I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 45\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = 1\text{V}, I_C = 100\text{mA}$	100		600	
	$h_{FE(2)}$	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE} = 1\text{V}, I_C = 500\text{mA}$			1.2	V
Collector capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1\text{MHz}$		10		pF
Transition frequency	f_T	$V_{CE} = 5\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$	100			MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	BC817-16	BC817-25	BC817-40
Range	100-250	160-400	250-600
Marking	6A	6B	6C

TYPICAL CHARACTERISTICS

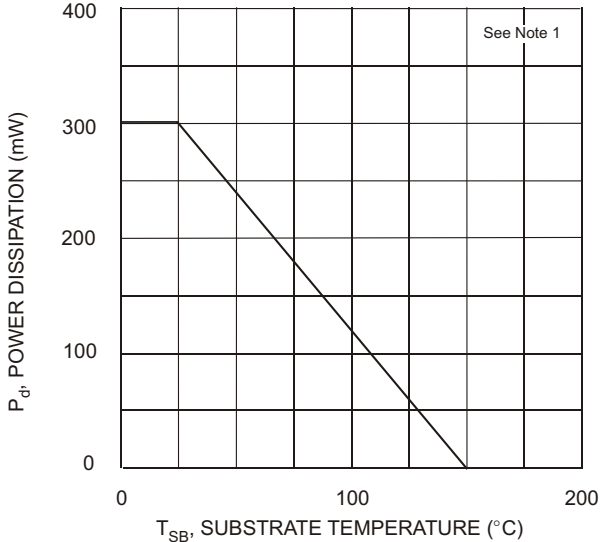


Fig. 1, Power Derating Curve

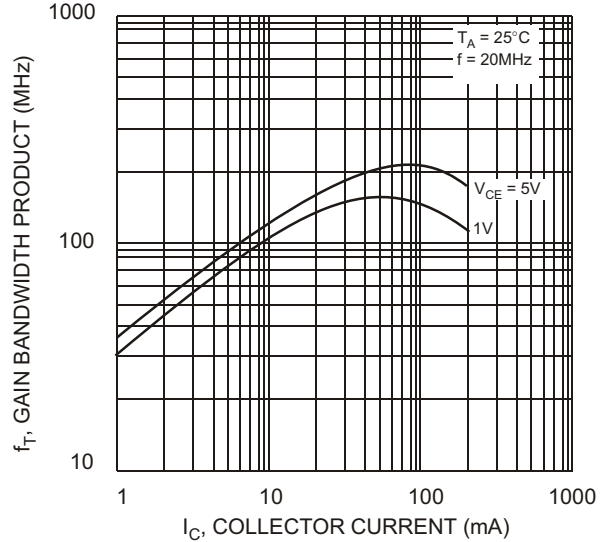


Fig. 2, Gain-Bandwidth Product vs. Collector Current

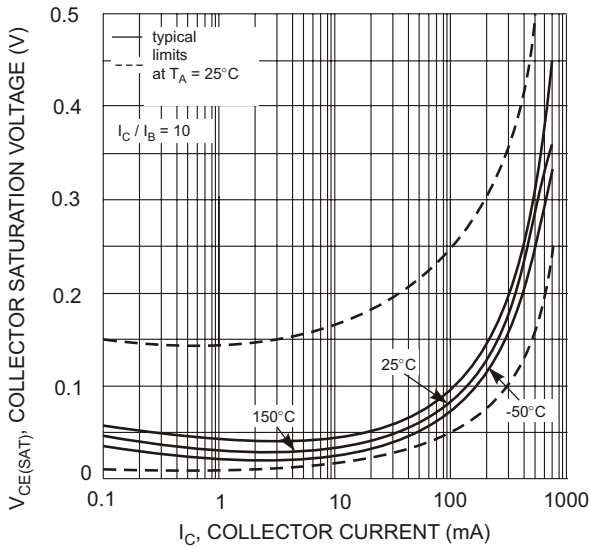


Fig. 3, Collector Sat. Voltage vs. Collector Current

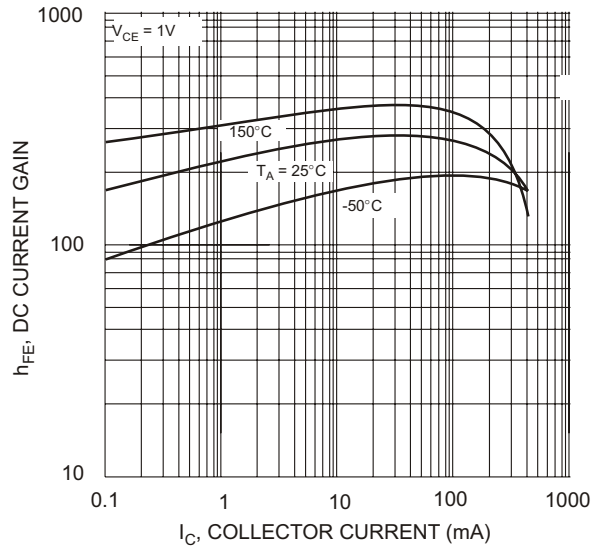


Fig. 4, DC Current Gain vs. Collector Current

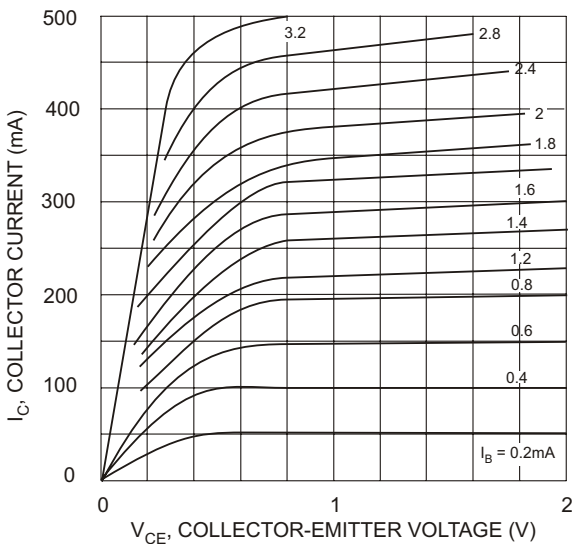


Fig. 5, Typical Emitter-Collector Characteristics

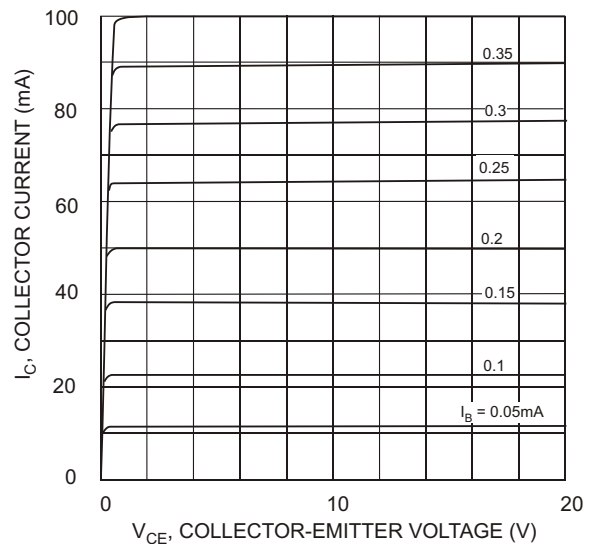
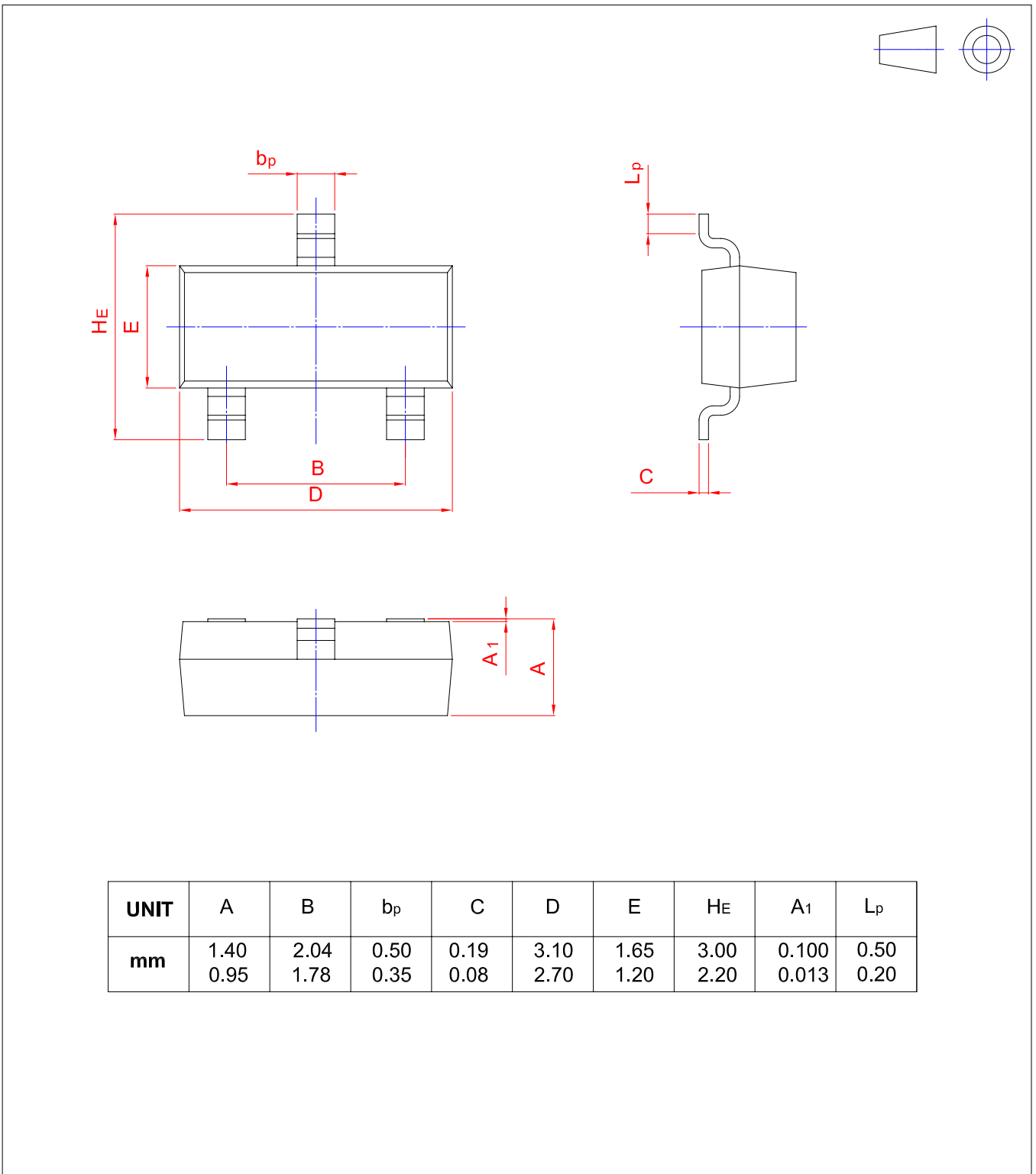


Fig. 6, Typical Emitter-Collector Characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [TWGMC manufacturer](#):

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [BC557/116](#) [BSW67A](#) [NJVMJD148T4G](#) [NTE123AP-10](#) [NTE153MCP](#) [NTE16](#)
[NTE195A](#) [NTE92](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [2SC2712S-GR,LF](#) [SP000011176](#) [2N2907A](#) [2N3904-](#)
[NS](#) [2N5769](#) [2SC2412KT146S](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [MJE340](#) [Jantx2N5416](#) [US6T6TR](#) [NJL0281DG](#) [732314D](#) [CPH3121-TL-E](#)
[CPH6021-TL-H](#) [873787E](#) [IMZ2AT108](#) [MMST8098T146](#) [UMX21NTR](#) [MCH6102-TL-E](#) [NJL0302DG](#) [30A02MH-TL-E](#) [NTE13](#) [NTE26](#)
[NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [STX83003-AP](#) [JANTX2N2920L](#) [JANSR2N2222AUB](#) [CMLT3946EG TR](#) [2SA1371D-AE](#)